

Effects of inhomogeneous broadening on reflection spectra of Bragg multiple quantum well structures with a defect

L. I. Deych, M. V. Eremenchouk, and A. A. Lisyansky

Physics Department, Queens College,
City University of New York, Flushing, New York 11367

Abstract

The reflection spectrum of a multiple quantum well structure with an inserted defect well is considered. The defect is characterized by the exciton frequency different from that of the host's wells. It is shown that for relatively short structures, the defect produces significant modifications of the reflection spectrum, which can be useful for optoelectronic applications. Inhomogeneous broadening is shown to affect the spectrum in a non-trivial way, which cannot be described by the standard linear dispersion theory. A method of measuring parameters of both homogeneous and inhomogeneous broadenings of the defect well from a single CW reflection spectrum is suggested.

PACS numbers: 78.67.De, 42.70.Qs, 71.36.+c, 42.25.Bs

I. INTRODUCTION

Optical properties of multiple quantum well (MQW) structures have been attracting a great deal of attention during the past decade.^{1,2,3,4,5,6,7,8,9,10,11,12,13,14,15,16} The main motivation for this interest is the potential in these systems for effective control of the light-matter interaction. Quantum wells in MQW structures are separated from each other by relatively thick barriers, which prevent a direct interaction between excitons localized in different wells. They however, can be coupled by a radiative optical field, and their optical properties, therefore, become very sensitive to the arrangement of the structures. Most of the initial research in this area was focused on properties of periodic MQW's, which consist of identical quantum wells separated by identical barriers. The radiative coupling in this case gives rise to MQW polaritons { coherently coupled oscillations of the exciton polarization and light. In structures with a small number of wells, the spectrum of these collective excitations consists of a discrete number of quasi-stationary (radiative) modes with a re-distributed oscillator strength: the modes can be classified as super- or sub-radiant.^{2,3,5} With an increase of the number of wells in the structure, the radiative lifetime of the latter decreases, and the lifetime of the former increases. When the number of periods in the structure becomes large enough, the modes of the MQW are more conveniently described in terms of stationary polaritons of infinite periodic structures.¹³ The spectrum of polaritons in this case consists of two branches separated by a polariton gap, which is normally proportional to the light-exciton coupling constant, $\hbar V$. There exists, however, a special arrangement of MQW's where the magnitude of the gap can be significantly increased. If the period of the MQW structure is made equal to the half-wavelength of the exciton radiation, the geometric, Bragg, resonance occurs at the same frequency as the exciton resonance. As a result, the band gap between two polariton branches becomes of the order of magnitude of $\hbar \omega_0$, where ω_0 is the frequency of the exciton transition. These, so called Bragg MQW structures were quite intensively studied both theoretically^{1,2,8,13} and experimentally.^{6,9,10,11,12} In the case of structures with a small number of periods, the reconstruction of the optical spectra in Bragg MQW's can be described as a concentration of the oscillator strengths of all oscillators in one super-radiant mode, while all other modes become dark.²

A presence of the large band gap in the spectrum of Bragg MQW polaritons invites attempts to introduce a defect into a structure in order to create local polariton states with

frequencies in the band gap. This would affect the rate of spontaneous emission as well as other optical characteristics of the system. Such an opportunity was first considered in Ref. 14, and was studied in detail in Refs. 15,16. It was shown¹⁶ that by introducing different types of defects one can obtain optical spectra of a variety of shapes, which can be pre-engineered through the choice of the type of a defect, its position in the structure, the number of defects, etc. This fact makes these systems of interest for optoelectronic application. However, in order to be able to predict the optical spectra of realistic structures, any theoretical calculations must deal with the problem of inhomogeneous broadening, which is always present in these systems due to unavoidable structural disorder present in quantum wells. Calculations of Refs. 15,16 included inhomogeneous broadening using the linear dispersion theory.^{17,18} The linear dispersion theory treats inhomogeneous broadening as a simple addition to homogeneous broadening, ignoring therefore, effects of the motional narrowing, which have been very well studied in periodic multiple quantum wells.^{19,20,21} By doing so, the linear dispersion theory grossly overestimates the negative influence of inhomogeneous broadening, thereby giving unrealistically pessimistic predictions. The latter fact was verified in Ref. 22, where effects of the vertical disorder on the defect-induced features of the spectra were considered numerically.⁴⁰

More accurately inhomogeneous broadening can be studied with the help of the effective medium approximation, which was originally introduced in Ref. 23 on the basis of some qualitative arguments. In this approximation, a random susceptibility of a single quantum well is replaced by its value averaged over an ensemble of exciton frequencies, and therefore, one only needs to take into account the horizontal disorder, since on average all wells in the structure are assumed identical. This approach was shown to agree well with experimental results for both CW and time-resolved spectra,²⁴ but so far it has not been justified theoretically. In this paper, we derive this approximation from the Maxwell equations with a non-local exciton susceptibility and demonstrate explicitly the physical meaning of this approximation and the regions of its applicability.

The main objective of this paper is to study the effects of the inhomogeneous broadening in Bragg MQW structures with defects. Here we consider only one structure, namely a GaAs/GaAs structure with one of the wells replaced by a well with a different exciton frequency. A similar defect was considered in Ref. 16, where it was called an α -defect; we retain this terminology in this paper. The consideration in Ref. 16 was focused mostly on

the concept of local polariton states arising in infinite Bragg MQW structures, and on the effect of the resonant light tunnelling arising due to these local states in long ideal Bragg MQW's. In this paper, we consider defect-induced modification of the optical spectra in more realistic systems. We take into consideration the inhomogeneous broadening and concentrate on structures with the number of periods readily available with current growth technologies. Keeping in mind the potential of these structures for applications, we study under which conditions the defect-induced resonant features of the spectra of realistic structures can be observed experimentally. We develop a general understanding of the spectral properties of Bragg MQW's in the presence of defects and disorder required for identifying structures most interesting from the experimental and application points of view. We also obtain a simplified analytical description for the main features of the spectra, valid in some limiting cases. This description is complemented by a detailed numerical analysis. One of the surprising results is that the features associated with the resonant tunnelling via the local polariton state survive in the presence of disorder for much shorter lengths of the structure than was originally expected.^{15,16} This makes experimental observation and application of these effects significantly more attractive.

We also suggest a method of determining experimentally parameters of homogeneous and inhomogeneous broadening of a defect well in our structures from a single CW reflection spectrum. Such an opportunity seems to be quite exciting from the experimental point of view, since currently the separation of homogeneous and inhomogeneous broadenings requires the use of complicated time-resolved spectroscopic techniques. Attempts to develop a method for an independent extraction of the parameters of homogeneous and inhomogeneous broadenings from spectra of periodic MQW structures were undertaken in Refs. 23,25, but they also required either a time resolved spectroscopy or a not very reliable Fourier transformation of the original CW spectra.

II. REFLECTION SPECTRUM OF A MQW STRUCTURE

Within the framework of the linear nonlocal response theory, propagation of an electromagnetic wave in a multiple quantum well structure is governed by the Maxwell equations

$$\text{grad div } \mathbf{E} - \Delta \mathbf{E} = \frac{1}{c^2} \left(\epsilon_1 \mathbf{E} + 4 \mathbf{P}_{\text{ext}} \right); \quad (1)$$

where ϵ_1 is the background dielectric constant assumed to be the same along the structure, P_{ext} is the excitonic contribution to the polarization defined by

$$P_{\text{ext}}(z) = \int_{-Z}^Z \chi(\omega; z; z^0) E(z^0) dz^0; \quad (2)$$

and the susceptibility χ is

$$\chi(\omega; z; z^0) = \chi(\omega) \psi(z) \psi^*(z^0); \quad (3)$$

where $\psi(z)$ is the exciton envelope function and z is the growth direction. Considering only the 1-s heavy hole exciton states and neglecting the in-plane dispersion of excitons, the susceptibility can be written as²⁶

$$\chi(\omega) = \frac{f_0}{\omega_0 - \omega - i\gamma}; \quad (4)$$

where ω_0 is the exciton resonance frequency, γ is the exciton relaxation rate due to inelastic processes, $\gamma = \gamma_1 + \gamma_2$, $\gamma_1 = \frac{3}{4} \frac{v_{\text{LT}}^2}{a_B^3 \omega_0^2} = c^2$, v_{LT} is the exciton longitudinal-transverse splitting and a_B is the bulk exciton Bohr radius.

The reflection spectrum of MQW structures is effectively described by the transfer matrix method. For waves incident in the growth direction of the structure, the transfer matrix describing propagation of light across a single quantum well in the basis of incident and reflected waves is²

$$T = \begin{pmatrix} 0 & 1 \\ \frac{1}{t} & \frac{r}{t} \end{pmatrix} e^{i\phi}; \quad (5)$$

where r and t are the reflection and transmission coefficients of a single quantum well,

$$r = \frac{e^{i\phi} - 1}{1 - e^{i\phi}}; \quad t = \frac{e^{i\phi}}{1 - e^{i\phi}}; \quad (6)$$

$\phi = kd$, $k = \frac{2\pi}{\lambda}$ is the wave number of the electromagnetic wave, d is the period of the MQW structure (the sum of widths of the barrier and the quantum well), $\gamma_0 = \gamma_0(\omega_0 - \omega - i\gamma)$; γ_0 is the effective radiative rate

$$\gamma_0 = \frac{1}{2k} \int_{-Z}^Z dz |\psi(z)|^2 \cos kz; \quad (7)$$

and we neglect the radiative shift of the exciton resonance frequency.

The parameter γ in the exciton susceptibility, Eq. (4), introduces the nonradiative homogeneous broadening due to inelastic dephasing of excitons. Inhomogeneous broadening

results from fluctuations of the exciton transition frequency ω_0 in the plane of a well caused by, for example, imperfections of the interface between the well and the barrier layers and/or presence of impurities. In general, fluctuations of the exciton frequency are described by the n -point distribution functions, $f(\omega_0(r_1); \omega_0(r_2); \dots)$, where r_i is a coordinate of a point in the plane of the quantum well. However, in the effective medium approximation,^{19,23,27} adopted in this paper, only a simple one-point function, $f(\omega_0)$, is needed. This function is used to define an average susceptibility, neglecting a possible dependence of the exciton envelope function on the energy,^{23,28,29}

$$\chi \sim \int d\omega_0 \langle f(\omega_0) \rangle \quad (8)$$

In this approach, the inhomogeneous broadening is characterized by the variance of the distribution function, σ^2 . As we already mentioned in the Introduction, the effective medium approximation has never been actually derived, and therefore, its theoretical status and applicability remains unclear. In the Appendix we demonstrate how this approximation can be obtained from a general theory of interaction between light and excitons in a disordered quantum well, and explain why it gives such an accurate description of the optical properties of quantum wells.

The function χ replaces χ_0 in Eq. (6) and determines a single-well transfer matrix of a broadened well,²³ which is then used to construct the transfer matrix describing the propagation of light through the entire Bragg MQW structure. The structure considered in this paper, a Bragg MQW with an ω -defect, consists of $N = 2m + 1$ quantum well-barrier layers which are all identical except for one, at the center, where the quantum well has a different frequency of the exciton resonance (Fig. 1). Such a defect can be produced either by changing the concentration of Al in the barriers surrounding the central well,^{30,31} or the width of the well itself²² during growth. In principle, both these changes will also affect the optical width of the defect layers, either because of the change in the background dielectric constant, or due to the change of the geometrical thickness of the well. However, in both cases this effect is negligible, and we deal here with the case of a pure ω -defect.

The total transfer matrix through the MQW structure consists of the product

$$M = T_h \dots T_h T_d T_h \dots T_h; \quad (9)$$

where T_h and T_d are the transfer matrices through the host and defect layers, respectively, described by the reflection and transmission coefficients $r_{h,d}$ and $t_{h,d}$. Substitution of the

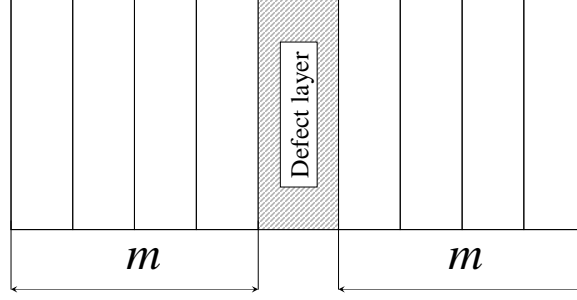


FIG .1: A MQW structure with a defect.

explicit expressions for T_h and T_d leads to a compact expression for the total transfer matrix in the basis of eigenvectors of the host transfer matrix T_h

$$M = \begin{pmatrix} 0 & 1 \\ a_+ A & A \end{pmatrix} e^{M_+} \begin{pmatrix} 1 & 0 \\ a_- A & A \end{pmatrix} \quad (10)$$

where $N = N_h$,

$$M = e^{(d-h)} \frac{2e^{-h}}{\sinh h} \sinh^2 \frac{1}{2} (d-h); \quad (11)$$

and

$$A = \frac{\sin}{\sinh h} (d-h); \quad (12)$$

Here we introduced a_{\pm} , non-unit components of the eigenvectors of T_h ,

$$a_{\pm} = \frac{1}{r_h} e^{\pm h t_h}; \quad (13)$$

and $r_{h,d}$ are the eigenvalues of the host and defect quantum well's transfer matrices obeying the dispersion law in a periodic quantum well superlattice^{1,2,3}:

$$\cosh r_{h,d} = \frac{1}{2} \text{Tr} T_{h,d} = \cos r_{h,d} \sin : \quad (14)$$

In the case of an ideal system without homogeneous or inhomogeneous broadenings, this equation describes the band structure of the electromagnetic spectrum of MQW's, consisting of a number of bands separated by forbidden band gaps, defined as frequency regions where $\text{Re } r_h \neq 0$. This real part describes the exponential decrease of the amplitude of an incident

wave, and its inverse gives the value of the respective penetration length. In the allowed bands, ϵ_h is purely imaginary, and its imaginary part is the Bloch wave vector of the respective excitation. There are two types of the excitations here. In the vicinity of the exciton frequency ω_h , there exist two polariton branches separated by a polariton band gap.¹³ There are also pure photonic bands with the band boundaries at the geometrical resonances, $(\omega_r) = n\pi$ ($n = 1; 2; \dots$). The size of the polariton gap strongly depends on the relation between ω_h and ω_r , and reaches the maximum value when they coincide, i.e. when $(\omega_h) = \omega_r$ (the Bragg structure). For these frequencies, it is convenient to extract the imaginary part from ϵ_h and to present it in the form

$$\epsilon_h = \epsilon_h + i\gamma_h \quad (15)$$

If the coupling parameter γ_0 is small, ϵ_h in the gap can be approximated by the following expression, which is obtained by expanding Eq. (14) near the resonance frequency

$$\epsilon_h = \frac{\gamma_0^2}{q(\omega_h - \omega_r)}; \quad (16)$$

where q is the detuning from the Bragg resonance

$$q = \frac{\omega - \omega_h}{\omega_h}; \quad (17)$$

Taking into account the form of the susceptibility in an ideal system, we obtain

$$\epsilon_h = \frac{q}{Q_G^2 - q^2}; \quad (18)$$

where

$$Q_G = \frac{\gamma_0}{\omega_h} \quad (19)$$

determines the boundary of the forbidden gap¹³ as a point where ϵ_h vanishes. The frequency, which corresponds to this boundary determines the width of the gap as $\frac{\gamma_0}{2\omega_h}$. This value is significantly greater than the respective width in the ordinary Bragg case, which is proportional to ω_h . In the presence of homogeneous and inhomogeneous broadenings, the notion of the band gap becomes ill defined, because ϵ_h does not vanish anywhere. At the gap boundary, for instance, it becomes complex valued

$$\epsilon_h(\omega_G) = (1 + i) \frac{\gamma_0}{2\omega_h}; \quad (20)$$

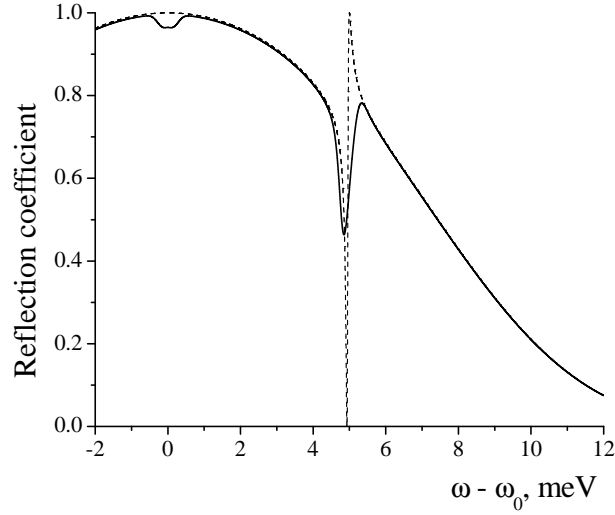


FIG. 2: A typical dependence of the reflection coefficient of a MQW structure with an embedded defect well in a neighborhood of the exciton frequency of the defect well. The dotted line shows the reflection for a lossless system, and the solid line corresponds to a broadened system (parameters are taken for GaAs/AlGaAs).

Nevertheless, if $\frac{\Gamma}{\hbar} \ll \omega$, which is the case in realistic systems, the optical spectra retain most of their properties specific for the gap region, and this concept provides a useful physical framework for discussing optical properties of MQW structures.

Once the transfer matrix, M , for the entire MQW structure is known the reflection and transmission coefficients can be expressed in terms of its elements, m_{ij} , as

$$\begin{aligned} r_{\text{MQW}} &= \frac{m_{11} + m_{12}}{a(m_{12} + m_{22})} - \frac{m_{21} + m_{22}}{a(m_{11} + m_{21})}; \\ t_{\text{MQW}} &= \frac{a}{a(m_{12} + m_{22})} - \frac{a}{a(m_{11} + m_{21})}; \end{aligned} \quad (21)$$

A defect inserted into the structure leads to a modification of the reflection spectrum of the MQW in the vicinity of the exciton frequency, ω_d , of the defect well. We are interested in the situation when ω_d lies within the polariton band gap of the ideal host structure, because in this case the defect produces the most prominent changes in the spectra. A typical form of such a modification in broadened systems is shown in Fig. (2), and is characterized by the presence of a closely positioned minimum and maximum. In an ideal system, this form of reflection would correspond to a Fano-like resonance in the transmission with the latter swinging from zero to unity over a narrow frequency interval.¹⁶ In the presence of absorption

and inhomogeneous broadening, the resonance behavior of the transmission is smeared out, while the resonance in reflection, as we can see, survives.

In order to analyze the form of the reflection spectra, we represent the reflection coefficient in the form

$$r_{MQW} = \frac{r_0}{1 - r_{add}}; \quad (22)$$

where

$$r_0 = \frac{2 \sinh(\gamma_h)}{a e^{\gamma_h} + a e^{-\gamma_h}} = \frac{\gamma_h}{1 + i \coth(\gamma_h) \sinh \gamma_h} \quad (23)$$

is the reflection coefficient of a pure MQW structure (without a defect) with the length N , $r_0 = \sin \gamma_h + \gamma_h \cos \gamma_h$, and r_{add} introduces the modification of the reflection caused by the defect

$$r_{add} = \left(\gamma_d - \gamma_h \right) \sin \gamma_h \frac{\sinh \gamma_h + i \gamma_h \sinh \gamma_h}{\cosh \gamma_h} \frac{1}{A \left(1 + \gamma_h \cosh \gamma_h \right) \sinh \gamma_h}; \quad (24)$$

This expression allows formaking some general conclusions regarding the effects of the defect and broadenings on the reflection spectrum. First of all, it should be noted that regardless of the value of the defect frequency ω_d , r_{add} vanishes at frequencies $\omega = \omega_h$ because of the phase factor $\sin \gamma_h$.

Thus, in order to achieve a significant modification of the spectrum, it is necessary to choose ω_d as far away from ω_h as possible. In this case, however, we can immediately conclude that the broadening of the host wells does not significantly affect the defect-induced features of the reflection spectrum.

Indeed, the broadenings enter into Eq. (24) through the susceptibility χ_h defined by Eq. (8). Let us rewrite this definition in the form

$$\chi_h = \int_{-\infty}^{\infty} d\omega f(\omega) \frac{1}{\omega - \omega_h - i\gamma_h}; \quad (25)$$

where we have introduced $\omega_h = \omega_0 + \gamma_h$, $\gamma_h = \gamma_0 + i\gamma_h$, $\gamma_0 = (\omega_0 - \omega_h) = \gamma_h$, and ω_h is the mean value of the exciton frequency. If the function $f(\omega)$ falls off with increasing $|\omega|$ fast enough, so that all its moments exist, we can approximate the integral for the frequencies $\omega = \omega_h + i\gamma_h$ as

$$\chi_h \approx \int_{-\infty}^{\infty} d\omega f(\omega) \left(1 + \frac{i\gamma_h}{\omega - \omega_h} + \dots \right); \quad (26)$$

where

$$\tilde{\chi}_h = \frac{\chi_0}{\Gamma_h + i\Gamma_d} \quad (27)$$

is the susceptibility in the absence of the inhomogeneous broadening. Noting that now integration of each term in the parentheses gives an appropriate central moment of $\tilde{\chi}_h$ we obtain

$$\tilde{\chi}_h = \chi_0 \left(1 + \frac{\tilde{\chi}_2}{\Gamma_h^2} + \dots \right) \quad (28)$$

Therefore, the corrections due to the inhomogeneous broadenings become small for frequencies, which are farther away from the central frequency than the inhomogeneous width Γ_h . Since the width of the polariton gap in Bragg MQW structures is significantly greater than the typical value of the inhomogeneous width, we can choose such a position of the defect frequency, ω_d , which is far enough from ω_h , and at the same time remains within the gap frequency region.

Significant diminishing of the effects due to disorder in optical spectra of periodic MQW for frequencies away from the resonance exciton frequency was obtained theoretically in Ref. 23 and observed experimentally in Ref. 34. This can also be seen in Fig. 2, where deviations from the spectra of an ideal structure (dashed line) caused by disorder in the host wells are significant only in the vicinity of ω_0 . The modification of the defect induced features of the spectra, which takes place in the vicinity of ω_d are caused by broadenings of the excitons in the defect layer, and this is the only broadening, which has to be taken into consideration in this situation.

III. DEEP AND SHALLOW DEFECTS

While Eq. (24) is suitable for a general discussion and numerical calculations, it is too cumbersome for a detailed analytical analysis. For such purposes we consider the reflection coefficient for two limiting cases when the expression for r_{add} can be significantly simplified. The first limit corresponds to the situation when the penetration length of the electromagnetic wave at the frequency of the defect is much smaller than the length of the structure (we call it a deep defect), and the second is realized in the opposite case, when the system is much shorter than the penetration length (shallow defect).

A . Deep defect

When ω_d lies so far away from both ω_h and the boundary of the band gap that the penetration length of the electromagnetic wave is much smaller than the length of the structure $[Re(\epsilon) \gg 1]$, two different approximations are possible. When the homogeneous broadening is small enough such that

$$\gamma < 8 \omega_h \frac{Q}{Q_G^2} \frac{e^{-2} \gamma^3}{Q_G^2}; \quad (29)$$

where $\gamma = (\omega_d - \omega_h) = \omega_h$, the system is close to ideal, and the results of Ref. 16 remain valid. This inequality, however, becomes invalid for long systems, and then the exponentially small non-resonant terms in Eq. (24) can be neglected. The reflection in the vicinity of ω_d in this case can be presented in the form

$$r = r_0 \frac{D_d}{D_d + 2ie^{-2}\omega_h}; \quad (30)$$

where $D_{dh} = 1 - D_{dh}$ and

$$r_0 = \frac{1}{1 + D_h [\gamma + i\omega_h (1 + 2e^{-2})]} \quad (31)$$

is the approximation for the reflection coefficient of the structure without the defect for frequencies deeply inside the forbidden gap. We keep the term $\exp(-2)$ in this expression in order to preserve the correct dependence of the reflection coefficient of the pure structure on its length. The frequency ω_d ,

$$\omega_d = \omega_h \frac{D_d}{D_d + 2e^{-2}}; \quad (32)$$

describes the shift of the position of the reflection resonance from the initial defect frequency ω_d . This shift is an important property of our structure, which takes place in both ideal and broadened systems; Eq. (32) is a generalization to the systems with inhomogeneous broadening of the result obtained in Ref. 16.

Deriving Eq. (30), in addition to the assumption about the relation between the length of the structure and the penetration length, we also assumed that the exciton frequency of the defect well lies far enough from the frequency of the host wells, and neglected the contribution of the host susceptibility χ_h into the terms proportional to $\omega_d - \omega_h$. We also dropped a frequency dependence of the non-resonant terms.

Eq. (30) shows that when the defect well exciton frequency lies deeply inside the forbidden gap the effect of the defect on the reflection spectrum of the system exponentially decreases when the length of the MQW structure increases. This behavior is strikingly different from that of the respective ideal systems, where resonant tunnelling results in the transmission equal to unity at the resonance regardless of the length of the system. One can see that inhomogeneous broadening severely suppresses this effect, as was anticipated in Ref. 16.

If the shift, ω_d , of the resonance frequency from ω_d is large enough, so that ω_r is well separated from ω_d , the effects of the inhomogeneous broadening can be neglected. In this case, we can derive a simple approximate expression for the reflection coefficient in the vicinity of ω_r . The condition $\omega_d \gg \omega_r$ can, in principle, be fulfilled because $\omega_h(\omega_d)$ decreases when the frequency goes to the edge of the stop band where ω_h is determined by Eq. (20) and for GaAs/AlGaAs MQW structures with $\omega_h = 1.49 \text{ eV}$, $\omega_g = 67 \text{ eV}$, $\omega_g = 12.6 \text{ eV}$ and $\omega_g = 290 \text{ eV}$ we obtain $\text{Re}[(\omega_h + \omega_g)] \approx 6.3$.

In this case, in the vicinity of the resonance frequency we can approximate the susceptibility χ_d by

$$\chi_d = \frac{\chi_0}{\omega_d - \omega_r - i\gamma} \quad (33)$$

and obtain that the resonance has a form of the Lorentz-type dip on the dependence of the reflection spectrum positioned at $\omega = \omega_d$ with the depth, H , and the width, W , defined by expressions

$$H = \chi_0^2 \frac{1 + e^{-\omega_h^2}}{(1 + e^{-2\omega_h^2})^2}; \quad (34)$$

$$W = \frac{1}{\omega_h} + e^{-\omega_h^2}; \quad (35)$$

It should be noted, however, that while formally this approximation is valid even when ω_d is close to the edge of the forbidden gap, the deep defect approximation requires that $\omega_d \gg \omega_h$. For GaAs/AlGaAs structures this means that $N > 1 = \text{Re}(\omega_h) \approx 2000$. The structures of this length are beyond current technological capabilities, so this case presents mostly theoretical interest.

In the opposite situation, when the frequency shift is small ($\omega_d < \omega_h$), i.e. when ω_d is not too close to the edge of the gap, the inhomogeneous broadening becomes important, and in

order to estimate its contribution we use a Gaussian distribution of the exciton resonance frequencies in Eq. (8):

$$D_d = \frac{P_0}{P} = \frac{Z}{1} \int_{-\infty}^{\infty} d\omega_0 \frac{e^{-(\omega_0 - \omega_d)^2 = \gamma^2}}{\omega_0 - \omega_i} : \quad (36)$$

Using the function $w(\omega) = e^{-\gamma^2} \text{erfc}(\gamma(\omega - \omega_i))$, the integral can be written as

$$= \omega_0 w(\omega) \Big|_{-\infty}^{\infty} = ; \quad (37)$$

where $\gamma = (\gamma_0^2 + \gamma_d^2 + \gamma_i^2)^{1/2}$. The small γ expansion³⁵

$$w(\omega) \approx 1 + 2i\gamma \frac{P}{\omega - \omega_i}$$

allows us to obtain:

$$D_d = \frac{2}{\gamma_0} (\gamma_d + \gamma_i \sim \gamma); \quad (38)$$

where γ is the effective broadening,

$$\gamma = \gamma_0 + \frac{P}{2} : \quad (39)$$

One can see that in this case the inhomogeneous and homogeneous broadening combine to form a single broadening parameter γ , as it is assumed in the linear dispersion theory. The resonance on the reflection curve also has, in this case, a Lorentz-type dip centered at

$$\omega = \frac{\omega_0}{2\gamma_h + \gamma_g^2}; \quad (40)$$

with the depth and the width, respectively, equal to

$$H = \frac{P_0}{P} \frac{2}{\gamma} e^{-\gamma^2 \gamma_h}; \quad W = \gamma + e^{-\gamma^2 \gamma_h}; \quad (41)$$

Because of the inhomogeneous broadening contribution, the effective parameter γ becomes so large that $e^{-\gamma^2 \gamma_h} \sim \gamma_h$, and the defect-induced reflection resonance becomes rather weak compared to the case considered previously.

B. Shallow defect

From the experimental point of view, a more attractive situation arises when the length of the structure is smaller than the penetration length. This situation, which can be called

the case of a shallow defect, can be described within the same approximations as used in the previous section, with an obvious exception of the treatment of terms proportional to $e^{-\gamma}$. Here we can expand the exponential function in terms of the powers of γ . Finally we arrive at the following expression, which describes the defect-induced modification of the reflection spectra:

$$r = \frac{i}{\Gamma_h + i(\Gamma_0 + \Gamma_s)} \frac{\Gamma_0 D_d}{\Gamma_0 D_d}; \quad (42)$$

where Γ_0 is the radiative width of the pure Bragg MQW structure, which is N -fold enhanced because of the formation of a superradiant mode⁴

$$\Gamma_0 = \frac{\Gamma N}{1 - i\Gamma N}; \quad (43)$$

This expression coincides with the results of Ref. 4 with the exception of the term proportional to ΓN , which was neglected in the previous papers. We keep this term to be able to consider the case when the detuning from the resonance point Γ_h is not very small³⁶.

The distinctive feature of the shallow defect is that the reflection resonance does not have a Lorentz-like shape, which is typical for the deep defect when the resonant tunnelling is suppressed. Instead, we have a reflection spectrum with a minimum at Γ_- and a maximum at Γ_+ . This is a surprising result, because the Fano-like behavior associated with the resonant tunnelling is restored even though the length of the system is too short for effective tunnelling to take place. It is convenient to describe the positions of these frequencies relative to the modified defect frequency,

$$\Gamma_d = \Gamma_0 + \Gamma_s; \quad (44)$$

where Γ_s is defined as

$$\Gamma_s = \frac{\Gamma_d \Gamma_h}{N}; \quad (45)$$

The positions of the extrema are shifted from Γ_d : Γ_- toward the center of the gap, and Γ_+ in the opposite direction. As a result, Γ_- is well separated from Γ_d , while Γ_+ always lies in the close vicinity of the defect frequency.

For short systems, Γ_s can become larger than Γ_0 ; for example, in GaAs/AlGaAs MQW structures, the condition $\Gamma_s > \Gamma_0$ is fulfilled when $N < N_0 = 10$. In this case, an approximate analytical description of the spectrum is possible again. However, since the maximum

and the minimum of the spectra lie at significantly different distances from ω_d , the description of these two spectral regions would require different approximations. The maximum of the reactivity takes place close to the defect frequency, and therefore the inhomogeneous broadening near the maximum has to be taken into account. At the same time, $\omega \approx \omega_d$, and the inhomogeneous broadening in this frequency region can be neglected. Thus, we can approximate D_d by Eq. (33) in the vicinity of ω_- and by Eq. (38) near ω_+ . Using these approximations we find that the minimum and the maximum of the reflection coefficient are at the frequencies

$$\omega_- = \omega_d - \omega_s \frac{\gamma_s^2}{\gamma_s^2 + 4\gamma_0^2} \quad (46)$$

and

$$\omega_+ = \omega_d + \frac{1}{2} \frac{\gamma_s^2}{\gamma_s^2 + 4\gamma_0^2} \omega_s + \frac{\gamma_0^2}{\gamma_s^2 + 4\gamma_0^2} \gamma_s \omega_s \quad (47)$$

respectively, where $\gamma_s = \gamma_0 \frac{\omega_s}{\omega_d}$ and γ_0 is the effective broadening defined by Eq. (39).

The values of the reflection at these points are

$$R_{\min} = \frac{\gamma_s^2 \gamma_0^2 N^4}{(\omega_d - \omega_h)^4 (N - 1)^2};$$

$$R_{\max} = \frac{\gamma_s^2 (\gamma_s + \gamma_0)^2}{(\omega_+ - \omega_h)^2 (2\gamma_0 + \gamma_s)^2}; \quad (48)$$

The exact and approximate forms of the reactivity are compared in Fig. 3. One can see that these approximations give a satisfactory description of the reactivity in the vicinities of the extrema for short systems.

The minimal value of the reflection is determined only by the small parameter of the homogeneous broadening, γ_0 , and can therefore become very small. This fact reflects the suppression of the inhomogeneous broadening in this situation. When the length of the system increases, R_{\min} grows as N^4 , however, when $N > N_0$, the inhomogeneous broadening starts coming into play: γ_0 must be replaced with a larger effective broadening containing a contribution from γ_s . This also leads to a significant increase in R_{\min} . This behavior is illustrated in Fig. 4, where a comparison of the reflection coefficients for two MQW structures with different lengths is provided. The expression for R_{\min} , Eq. (48), allows one to obtain an estimate for the parameter of the homogeneous broadening γ_0 by measuring the value of R_{\min} , since all other parameters entering this expression are usually known. This approach

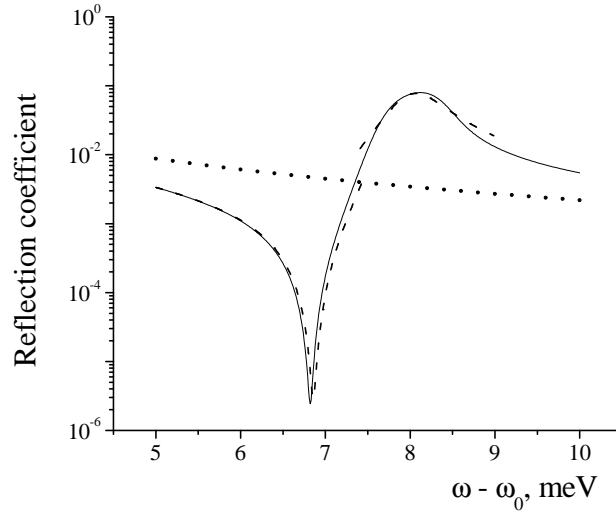


FIG. 3: Reflection coefficient near the exciton frequency of the shallow defect (solid line) for $N = 7$. The dashed lines depict approximation using different expressions for the defect quantum well susceptibility at the vicinities of the extrema: near the minimum the inhomogeneous broadening is neglected, while in the vicinity of the maximum it is accounted for as a renormalization of homogeneous broadening [Eq. (39)]. For reference, the reflection coefficient of a pure MQW structure without a defect is shown (dotted line).

to determining γ from reflection experiments, however, cannot be used when the predicted values of R_{\min} is too small, because other factors (such as small mismatch in the indexes of refraction between different components of the structure) which were neglected in our calculations can become important. At the same time, it can be expected that for not very short systems, satisfying the condition $N < N_0$, the parameter γ can be determined from the reflection spectrum.

The inhomogeneous parameter enters expressions Eq. (47) for γ_+ and Eq. (48) for R_{\max} . Therefore, one can determine this parameter from two independent values accessible from the reflection spectra. The maximum value of the reflection coefficient in this approximation depends very weakly on the number of wells in the system, and is of the order of the magnitude of the reflection from a single standing defect well in the exact resonance. This result means that for a small number of wells, γ_+ lies in the spectral region, where the host system is already almost transparent, and the presence of the host has only a small effect on the reflection properties of the system with the defect. At the same time, we would like

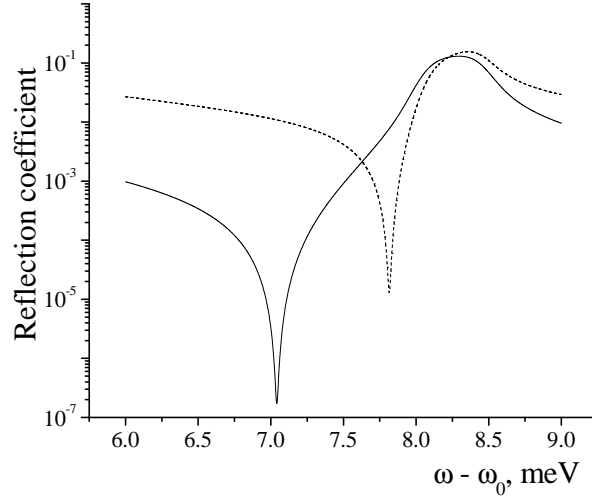


FIG. 4: Dependence of the reflection coefficient on the frequency in the neighborhood of the exciton frequency of the defect well for different lengths of the MQW structure (solid line $N = 3$, dashed line $N = 5$). The great difference of minimal reflections results from the shift of the resonance frequency ω_s , Eq. (45).

to emphasize again that the minimum of the reflection is the result of the radiative coupling between the wells even in this case of short systems.

C. Characterization of the reflection spectra in the case of intermediate lengths

In the previous subsections we examined special situations when the defect can be considered as either deep or shallow. In both cases, we were able to derive approximate analytical expressions describing defect-induced modification of the spectra and to obtain a qualitative understanding of how the defect affects the reflection spectrum. In particular, it was demonstrated that the characteristic frequencies related to the modification of the spectrum are shifted from the resonant defect frequency of a single well. This shift is the result of radiative coupling between the excitons in the defect well and the collective excitations of the host system. One of the important consequences of this shift is the possibility for almost complete suppression of the effects due to inhomogeneous broadening in some spectral intervals. In this subsection we consider systems with intermediate lengths, when N is larger than N_0 , but is still smaller or of the order of magnitude of the penetration length. From the

practical point of view, this case is of the greatest interest, since this interval of lengths is still easily accessible experimentally, and at the same time, it is expected that for such structures the defect-induced modifications of the spectrum become most prominent. Unfortunately, neither approximation used in the previous subsections can be applied here, and we have to resort to a numerical treatment. Nevertheless, the qualitative understanding gained as a result of the previous analytical considerations, serves as a useful guide in analyzing and interpreting the numerical data.

As it was pointed out in the previous section, when N becomes larger than N_0 , the position of the minimum of the reflection, ω_{\min} , moves closer to ω_d , and the inhomogeneous broadening starts contributing to R_{\min} . This effect can phenomenologically be described as the emergence of an effective broadening parameter $\gamma_{\text{eff}}(\omega; N)$, which is not a simple combination of γ and γ_d , but depends upon N . This parameter is limited from below by γ , when the inhomogeneous broadening is suppressed, and from above by γ_d , when the contribution from γ_d is largest. Because the minimum value of the reflection is always achieved at a point shifted with respect to ω_d , generally γ_{eff} is always smaller than γ_d , and the homogeneous broadening makes the main contribution to it even for systems with $N > N_0$ despite the fact that γ_d is larger. At the same time, the position of ω_{\max} , which determines the width of the spectral interval affected by the defect, depends upon γ_d . Thus the effect of the broadenings on the spectrum can in general be summarized in the following way: while the width of the resonance is determined equally by both homogeneous and inhomogeneous broadenings, its strength depends mostly upon the homogeneous broadening.

We illustrate this conclusion quantitatively by defining the width of the resonance, $W(\omega; N) = \omega_{\max} - \omega_{\min}$, as a distance between the extrema of the reflection spectrum, and its depth, $H(\omega; N) = R_{\max} - R_{\min}$, as the difference between the values of the reflection at these points. In order to see how these quantities depend upon parameters γ and γ_d , we chose several different values of W and H , and plot constant level lines, $W(\omega; N) = W_i$, $H(\omega; N) = H_i$. These lines represent values of γ and γ_d for which W and H remain constant (Fig. 5).

The locus of constant widths is the set of nearly straight lines running almost parallel to the axis representing the homogeneous broadening. Slight deviation from the straight-line behavior is seen only for non-realistically high values of γ_d . Such a behavior confirms our assertion that the width of the resonance is determined by an effective parameter, in which

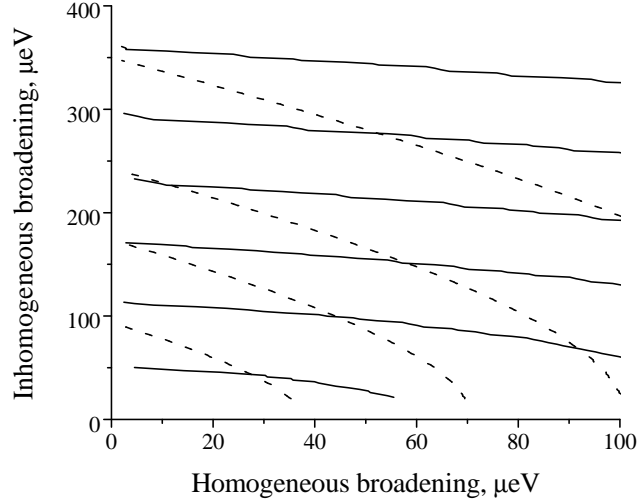


FIG. 5: Intersections of lines of constant height (dashed lines) and width (solid lines) of the resonance allow determination of the values of the homogeneous and inhomogeneous broadenings.

and enter additively. As we see, this is true even for systems which cannot, strictly speaking, be described by approximations leading to Eq. (47). Since usually γ_{inh} , the latter term makes the largest contribution to this effective parameter, and determines the value of W . The shape of the lines of constant height demonstrates almost equal contributions from γ_{inh} and γ_{hom} , which means that the effect due to the inhomogeneous broadening is significantly reduced as far as this feature of the spectrum is concerned. This is also consistent with an approximate analysis presented in the previous section of the paper.

The remarkable feature of Fig. 5 is that the lines of the constant width and the constant height cross each other at a rather acute angle and at a single value of γ_{inh} and γ_{hom} for each of the values of W and H . This means that one can extract both γ_{inh} and γ_{hom} from a single reflection spectrum of the MQW structure. This is a rather intriguing opportunity from the experimental point of view, since presently, the only way to independently measure parameters of homogeneous and inhomogeneous broadenings is to use complicated time-resolved techniques.

It is clear, however, that the shape of the lines of constant W and H depends upon the choice of the distribution function used for calculation of the average susceptibility of the defect well. It is important, therefore, to check how the results depend upon the choice of the distribution function of the exciton frequencies. As an extreme example, one can

consider the Cauchy distribution

$$f(\omega_0) = \frac{1}{(\omega_0 - \omega_c)^2 + \gamma^2} \quad (49)$$

In this case, all the effects due to the inhomogeneous broadening can be described by a simple renormalization, $\gamma \rightarrow \gamma + \gamma_c$, and the level lines in Fig. (5) would have the form of parallel lines. This distribution though, hardly has any experimental significance, while the Gaussian function has a certain theoretical justification.³⁷ However, the symmetrical character of the normal distribution is in obvious contradiction with a natural asymmetry of the exciton binding energies, which can be arbitrarily small but are bounded from above. It was suggested in Ref. 24 to take this asymmetry into account by introducing two different variances in the Gaussian distribution: σ_1 for frequencies below some (most probable) frequency ω_c , and σ_2 for the frequencies above it. Accordingly, the distribution function can be written as

$$f(\omega_0) = \frac{1}{\sigma_1 \sqrt{2\pi}} e^{-\frac{(\omega_0 - \omega_c)^2}{2\sigma_1^2}}; \quad \omega_0 < \omega_c; \quad (50)$$

$$f(\omega_0) = \frac{1}{\sigma_2 \sqrt{2\pi}} e^{-\frac{(\omega_0 - \omega_c)^2}{2\sigma_2^2}}; \quad \omega_0 > \omega_c;$$

It was shown that this choice gives a satisfactory description of time-resolved spectra of MQW's.²⁴ The distribution function Eq. (50) can be parameterized either by ω_c and σ_1 or, more traditionally, by the mean value, ω , the second moment, σ^2 , and the parameter of asymmetry, n , defined as

$$\omega = \frac{\omega_c + \sigma^2}{\sigma^2}; \quad n = \frac{\sigma^2}{\omega_c - \omega}; \quad (51)$$

$$\sigma^2 = \frac{\omega_c^3 + \omega^3}{\omega_c + \omega} - \frac{2}{3}(\omega_c + \omega)^2;$$

We use the corrected distribution function, Eq. (50), with the fixed mean frequency and the variance, but different values of the asymmetry parameter, in order to see how sensitive the defect induced features of the reflection spectrum are to the shape of the distribution function. To this end, we plot the lines of constant height and width for different values of the asymmetry parameter n ($1 \leq n \leq 2$). The results are presented in Fig. 6.

An interesting result revealed by these graphs is that with the change of the asymmetry, the points at which W and H level lines cross move parallel to the axis of ω , while the respective values of ω remain quite stable. This indicates that the value of ω , which can be

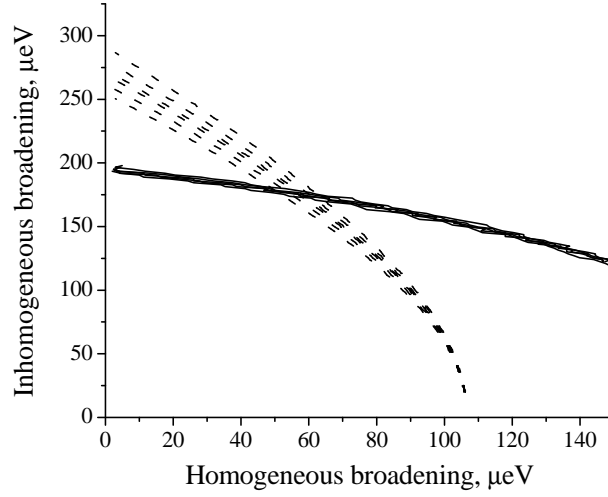


FIG. 6: Intersections for different values of the parameter of asymmetry. Dashed and solid lines are lines of constant height and width respectively.

obtained by comparing experimental reflection spectra with the theory presented in this paper, is not sensitive to the choice of the distribution function of the exciton frequencies. The value of the parameter of the homogeneous broadening is more sensitive to the asymmetry of the distribution function: it varies by approximately ten percent when the parameter of the asymmetry changes by a factor of two. However, the estimate for γ can be improved by studying the temperature dependence of the reflection spectra.

IV. CONCLUSION

In the present paper we studied the reflection spectra of a Bragg multiple quantum well system with a defect: the quantum well at the center of the structure was replaced by a well with a different exciton resonance frequency. In an ideal infinite system such a defect gives rise to a local state with a frequency within the polariton stop band of the host structure, which reveals itself in the form of reflection and transmission resonances.¹⁶ The main focus of this paper was on the effects due to the inhomogeneous broadening, which was taken into account within the framework of the effective medium approximation.²³ Since in Ref. 23 this approach was introduced on the basis of qualitative arguments only, in the Appendix we presented a rigorous derivation of this approximation and clarified its physical status.

We consider two limiting cases in which defect-induced features of the spectrum can

be described analytically. In one case, the length of the system is much larger than the penetration length of the radiation in the infinite periodic structure, l_c (deep defect). The modification of the reflection in this case is described by a Lorentz-like minimum, whose depth exponentially decreases with increasing length of the MQW structure, Eq. (41). For long enough structures the presence of the defect in the structure becomes unnoticeable. A much more interesting situation arises in the opposite case of systems much shorter than l_c (shallow defect). In this case, the reflection spectrum exhibits a sharp minimum followed by a maximum. This shape of the spectrum resembles a Fano-like resonance observed in long lossless systems. The position of the maximum of the reflection is close to the exciton frequency in the defect well, ω_d , where the short host structure is almost transparent, and therefore the properties of the spectrum near this point are similar to those of an isolated quantum well. At the same time, the minimum is shifted from ω_d by $\omega_s = (\omega_d - \omega_h) = N$ and due to this shift an influence of the inhomogeneous broadening, γ , on the spectrum near this point is strongly suppressed. When $\gamma \rightarrow 0$ the value of the reflection at the minimum, R_{min} , is determined solely by the small homogeneous broadening, and this results in extremely small values of R_{min} , Eq. (48).

The structure of the spectrum with two extrema persists also in the case of an intermediate relation between l_c and N . This situation, however, is more complicated and can only be analyzed numerically. Nevertheless, due to the shift of the minimum reflection frequency one can conclude that the minimum value of the reflection is determined mostly by the homogeneous broadening, while the distance between the maximum and the minimum is affected by an additive combination of the homogeneous and inhomogeneous broadenings. This circumstance allowed us to suggest a simple method of extracting both γ and ω_d of the defect well from the reflection spectrum of the structure.

Acknowledgments

We are grateful to Steven Schwarz for reading and commenting on the manuscript. The work is supported by AFOSR grant F49620-02-1-0305 and PSC-CUNY grants.

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APPENDIX A : THE EFFECTIVE MEDIUM APPROXIMATION FOR A SINGLE QUANTUM WELL

The objective of this appendix is to derive "from first principles" the main result of the effective medium approximation, Eq. (A 10) with ϵ replaced by the average susceptibility, given by Eq. (8).

A wave incident at a normal, z , direction on a quantum well can be described by a scalar form of Maxwell's equations for one of the polarizations parallel to the plane of a quantum well:

$$\epsilon^2 E(z) = \frac{\omega^2}{c^2} (\epsilon_1 E(z) + 4 P(z)); \quad (A 1)$$

where $P(z)$ is the polarization due to quantum well excitons. The latter is determined by an expression similar to Eq. (2) with the exciton frequency being a random function of the in-plane coordinate

$$P(z; \omega) = \int_{-\infty}^{\infty} d^2 r \chi(\mathbf{r}; \omega) (z^0) E(z^0; \omega); \quad (A 2)$$

where the susceptibility is

$$\chi(\mathbf{r}; \omega) = \frac{1}{\epsilon_1(\omega) - \omega^2} \quad (A 3)$$

In order to simplify our calculations we make an assumption that $\chi(z)$ can be approximated by a delta-function. This approximation is sufficient for our particular goals here, but the results obtained will remain valid for more rigorous treatment of the excitonic wave functions as well. After the Fourier transformation with respect to the in-plane coordinates, Eq. (A 1) can be presented in the form

$$\epsilon_q^2 + \frac{d^2}{dz^2} E_x(q; z) \quad (A 4)$$

$$= \frac{2\omega^2(z)}{c^2} \int_{-\infty}^{\infty} d^2 q' \chi(q'; \omega) E(q'; z); \quad (A 5)$$

where $\epsilon_q^2 = \epsilon_1^2 - c^2 q^2$.

Let us represent the susceptibility as a sum of its average value and a fluctuating part

$$\chi(q; \omega) = \bar{\chi}(\omega) + \tilde{\chi}(q; \omega); \quad (A 6)$$

where $h(\mathbf{q}; z)$ can be written in the form

$$h(\mathbf{q}; z) = \frac{d_0 f(\mathbf{q}; z)}{1 - d_0 f(\mathbf{q}; z)} : \quad (\text{A } 7)$$

The electromagnetic wave existing to the left of the quantum well consists of the incident and reflected waves. We will see later that the structure of the Maxwell equations with the polarization, Eq. (A 2), dictates that the reflection coefficient has a δ -functional singularity in the specular direction, $q = 0$. It is convenient to separate this singularity from the very beginning and to present the wave at the left-hand side of the quantum well in the following form .

$$E_-(\mathbf{q}; z) = E_0 e^{ikz} + E_0 r_0 e^{-ikz}(\mathbf{q}) + E_0 r(\mathbf{q}) e^{-i q z} : \quad (\text{A } 8)$$

A similar expression for the wave at the right-hand side of the quantum well containing only transmitted waves can be written as

$$E_+(\mathbf{q}; z) = E_0 t_0 e^{ikz}(\mathbf{q}) + E_0 t(\mathbf{q}) e^{i q z} : \quad (\text{A } 9)$$

After the substitution of Eqs. (A 7), (A 8), and (A 9) into Eq. (A 4) we obtain an integral equation for the reflection and transmission coefficients, $r(\mathbf{q})$, and $t(\mathbf{q})$. Assuming that the random process representing the fluctuating part of ϵ does not include constant or almost periodic realizations, we can conclude that $\epsilon(\mathbf{q}; \mathbf{r})$, does not have δ -like singularities in almost all realizations. In this case, the terms proportional to $\epsilon(\mathbf{q})$ in this equation must cancel each other independently of other terms. This leads to a system of equations for r_0 and t_0 with the solutions

$$r_0 = \frac{i}{1 - i}; \quad t_0 = \frac{1}{1 - i}; \quad (\text{A } 10)$$

where

$$= \frac{1}{c} \frac{1}{1 - i} h(\mathbf{q}; z) : \quad (\text{A } 11)$$

These expressions coincide with those of the effective medium approach, Eq (6), with an accuracy up to the phase factor, which does not appear in our derivation because of the δ -functional approximation for the excitonic wave function. We can conclude, therefore, that the substitution of the average susceptibility into the Maxwell equations allows us to consider the singular contribution to the reflection (transmission) only. The remaining

terms, which are neglected in this approximation, give only small corrections to the reflection (transmission) in the specular direction. However, these terms become important when one considers scattering of light from quantum wells. Another important assumption in our derivation concerns the spatial dispersion of the excitons. The existence of the singular contribution to the reflection (transmission) coefficients is directly related to neglecting any exciton motion in the in-plane direction. Spatial dispersion of excitons will smooth out this singularity, and, therefore, the smoothness of experimental scattering spectra can be used, in principle, to estimate the exciton's mass.

It is also important to emphasize that the outlined procedure does not involve any averaging of the electric field, and therefore the results obtained describe an intrinsically "deterministic" contribution to the reflection and transmission coefficients rather than some average characteristics thereof. The existence of such a singular component in the scattering spectrum was mentioned in Ref. 38 as well as observed in numerical calculations of Ref. 39.

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